N-Channel 20-V (D-S) MOSFET

Key Features:

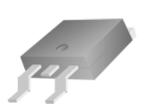
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

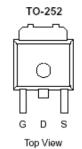
Typical Applications:

- DC/DC Conversion
- Power Routing
- Motor Drives

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
20	9 @ V _{GS} = 4.5V	61	
	11 @ V _{GS} = 2.5V	55	







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			20	V		
Gate-Source Voltage			±8	V		
Continuous Drain Current a	T _C =25°C	I_D	61	Α		
Pulsed Drain Current ^b			240			
Continuous Source Current (Diode Conduction) ^a	I _S	60	Α			
Power Dissipation ^a	T _C =25°C	P_{D}	50	W		
Operating Junction and Storage Temperature Range	·	T_J, T_{stg}	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	3	C/VV		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

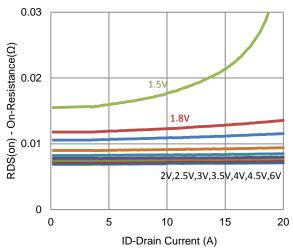
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	0.4			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Brain Guirent	I _{DSS}	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	90			Α	
Drain Course On Besistance a	$V_{GS} = 4.5 \text{ V}, I_D = 20$	$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$			9	mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 16 \text{ A}$			11	11122	
Forward Transconductance a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		9		S	
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 30 \text{ A}, V_{GS} = 0 \text{ V}$		1.3		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$		24			
Gate-Source Charge	Q_{gs}	$I_{D} = 20 \text{ A}$		3.5		nC	
Gate-Drain Charge	Q_gd	1D = 20 A		6.3			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 10 \text{ V}, R_{L} = 0.5 \Omega,$		7			
Rise Time	t _r	$I_{DS} = 10 \text{ V}, K_L - 0.3 \Omega,$ $I_D = 20 \text{ A},$		16		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		73		ns	
Fall Time	t _f	VGEN - 4.5 V, NGEN - 0 12		21			
Input Capacitance	C _{iss}			1964			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		164		pF	
Reverse Transfer Capacitance	C_{rss}]		146			

Notes

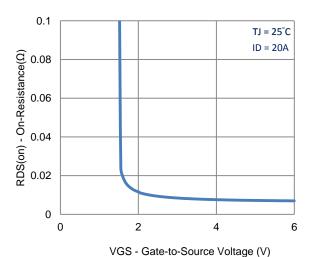
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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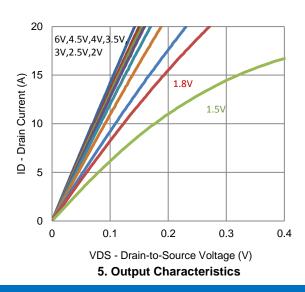
Typical Electrical Characteristics

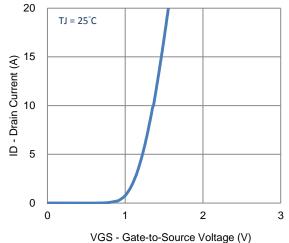


1. On-Resistance vs. Drain Current

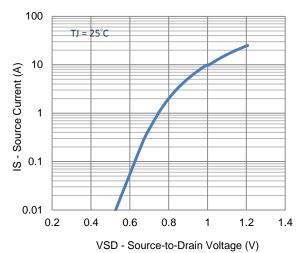


3. On-Resistance vs. Gate-to-Source Voltage

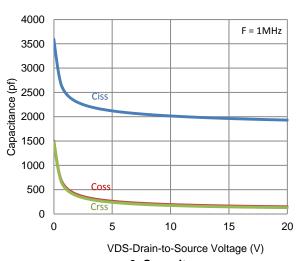




2. Transfer Characteristics

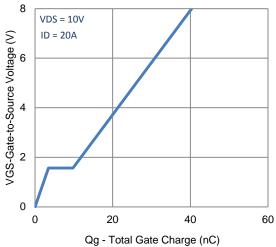


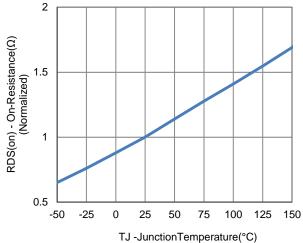
4. Drain-to-Source Forward Voltage



6. Capacitance

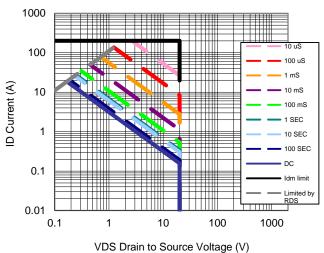
Typical Electrical Characteristics

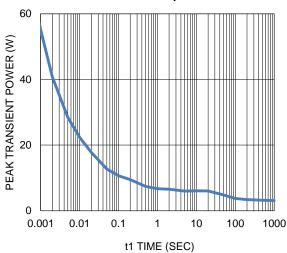




7. Gate Charge

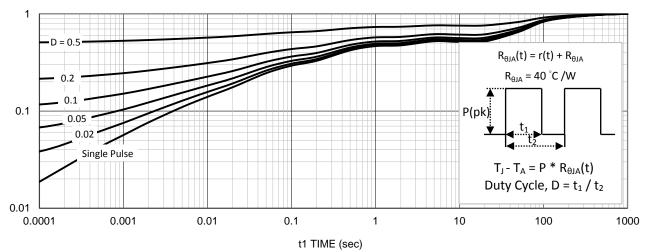
8. Normalized On-Resistance Vs
Junction Temperature





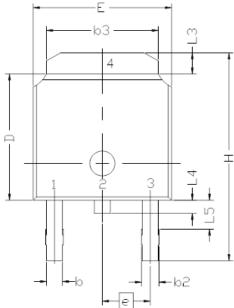
9. Safe Operating Area

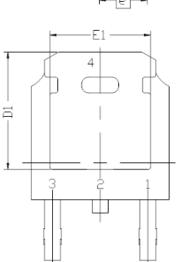
10. Single Pulse Maximum Power Dissipation



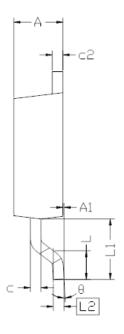
11. Normalized Thermal Transient Junction to Ambient

Package Information





SINGLE ROWNEW



CVADD	DIMENS:	[DNAL	REQMTS
SYMBOL	MIN	NDM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1		.743 R	
	0.	.508 BS	-
L3	0.89		1.27
L4	0.64		1.01
L5			
D	6.00	6.10	6,223
Н	9.40	10.00	10.40
b	0.64	0.76	0,88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
е	2.	286 BS	SC.
Α	2,20	2.30	2,38
A1	0		0.127
	0.45	0.50	0.60
c2	0.45	0,50	0.58
D1	5,30		
E1	4.40		
θ	0°		10°

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.